

# VERVE

**Vertexing in Extreme Radiation  
& Vacuum Environment**

Participating institutes

CERN and INFN (Bari, Cagliari, Catania, Frascati, Padova, Torino, Trieste)

Project leaders

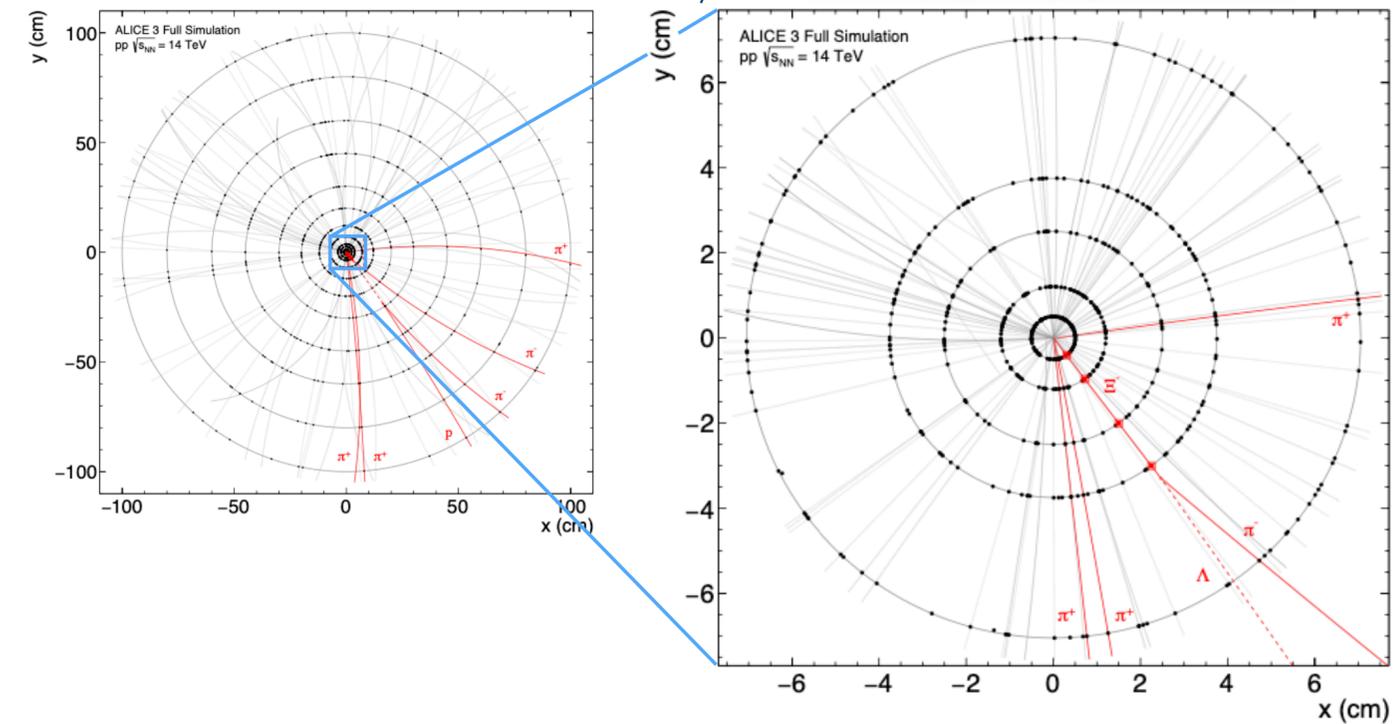
Domenico Colella (University and INFN Bari, Italy)

Jochen Klein (CERN)

# Introduction

What is needed to fully exploit potential of LHC?

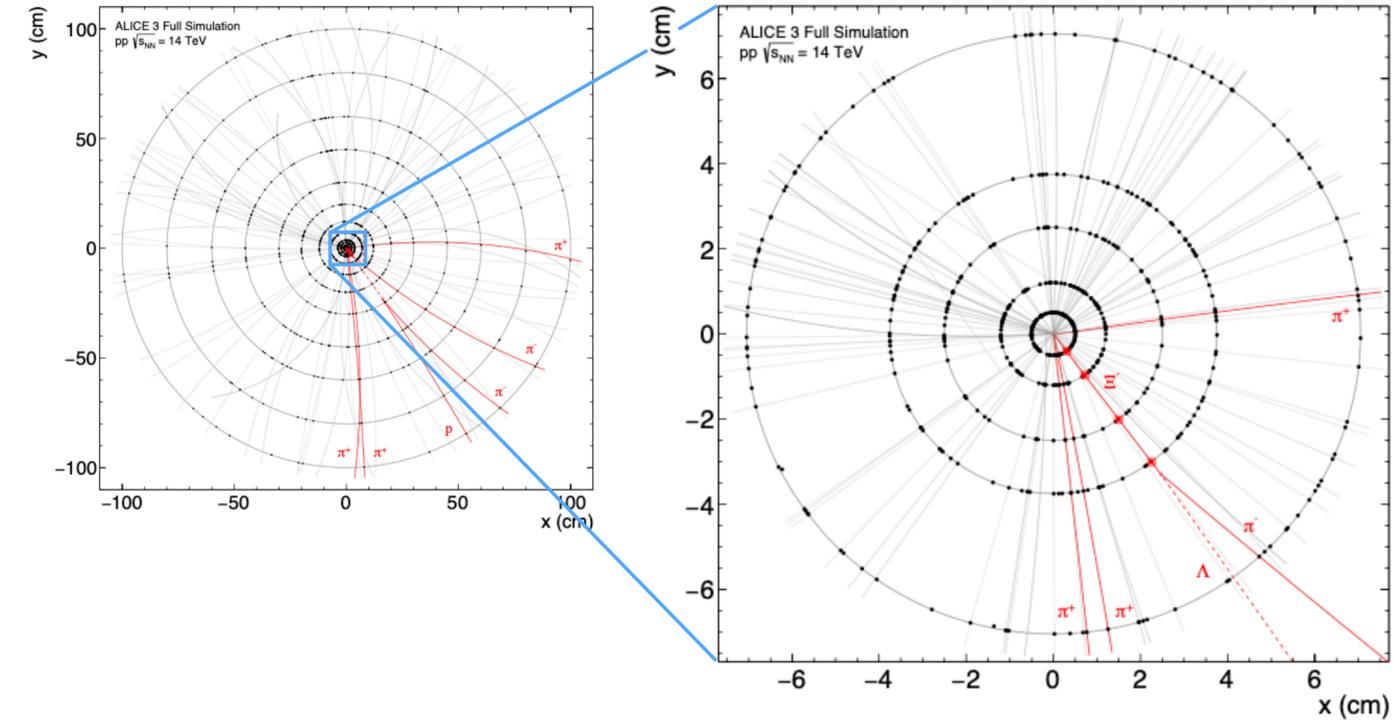
- LHC provides ideal and **unique environment to study hot QCD matter** and multi-charmed baryon production is a key tool
- Present devices are insufficient
  - Complex multi-stage decay chain in a track-dense environment  
→ Small signal in large combinatorial background
  - Reconstruction of decay vertices is crucial



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→ Small signal in large combinatorial background
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- Two required conditions to improve pointing resolution and allow such a measurement:
  - Reduce material budget
  - Reduce distance of first layer from interaction point



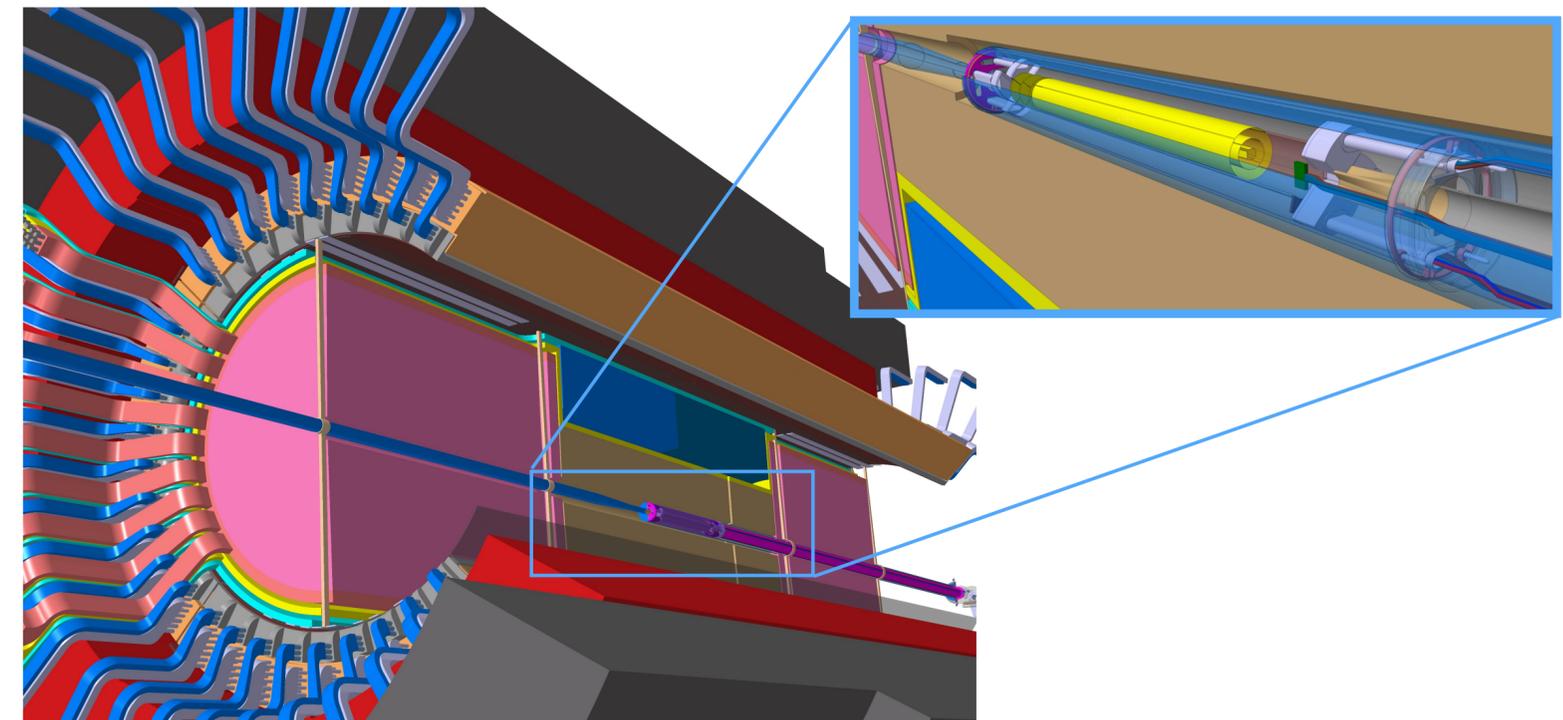
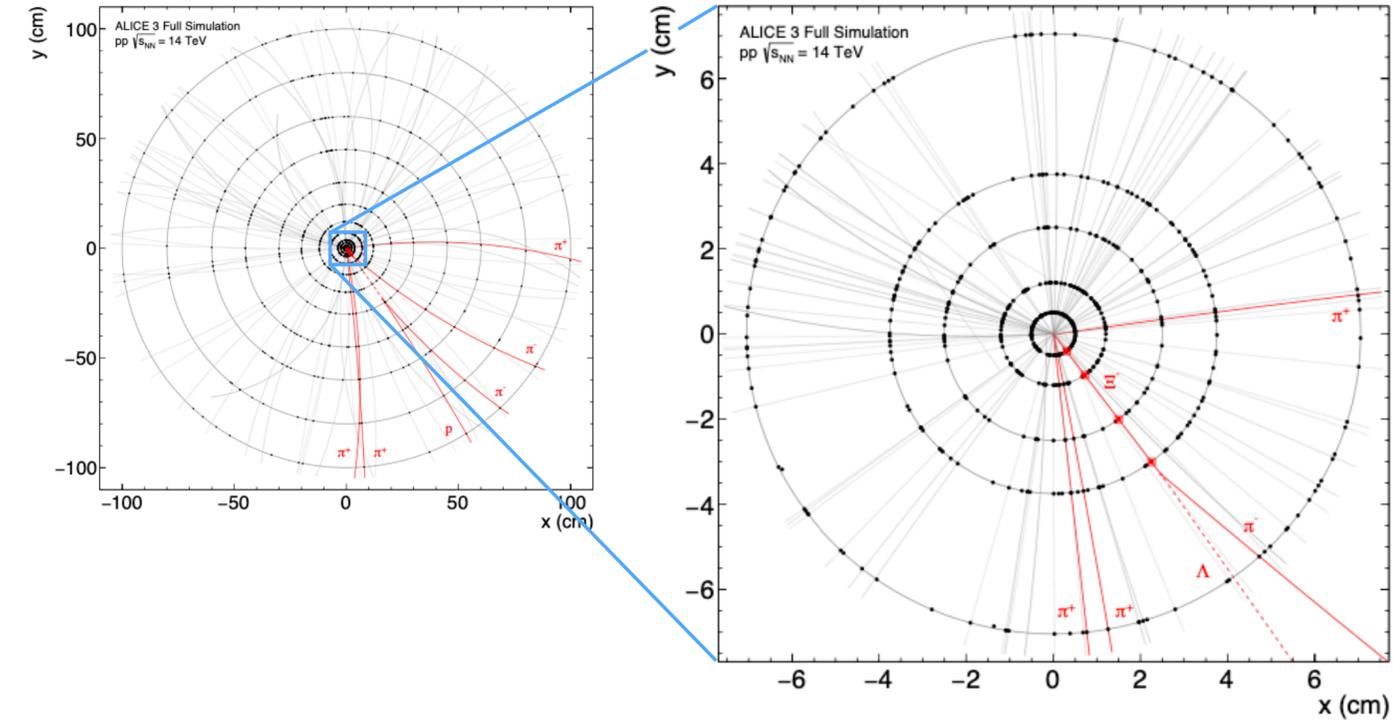
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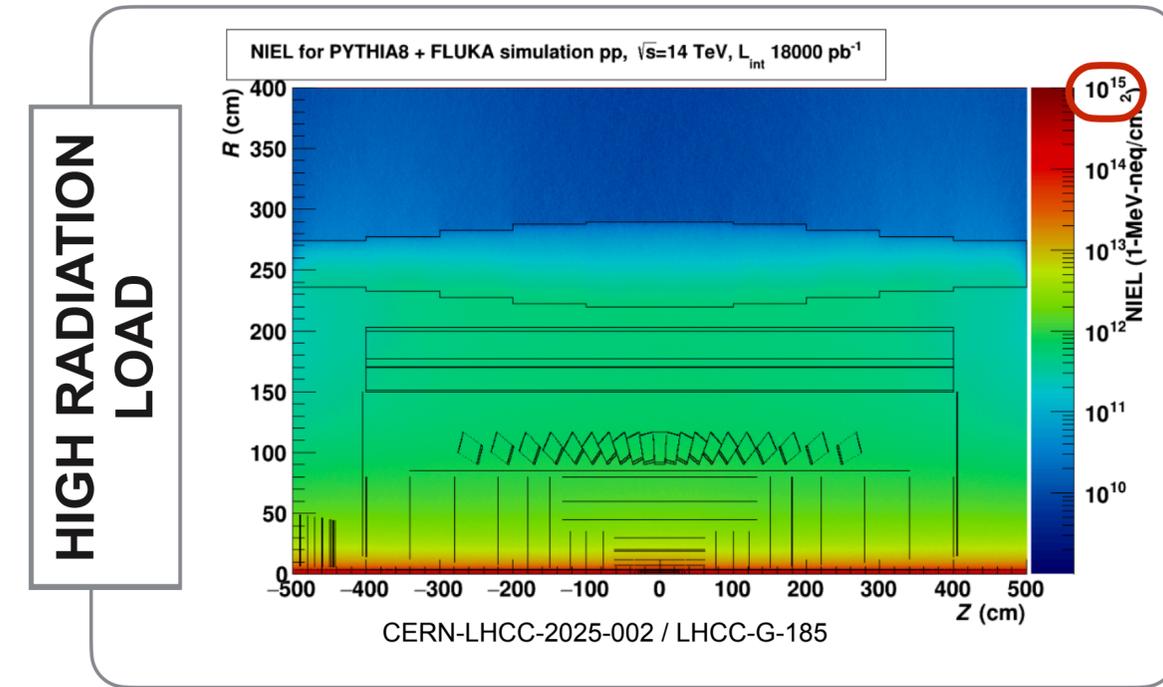
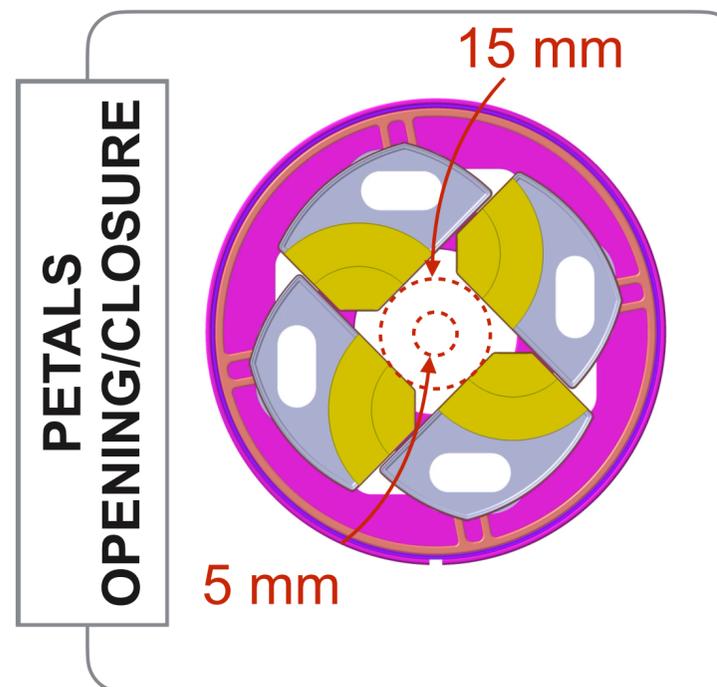
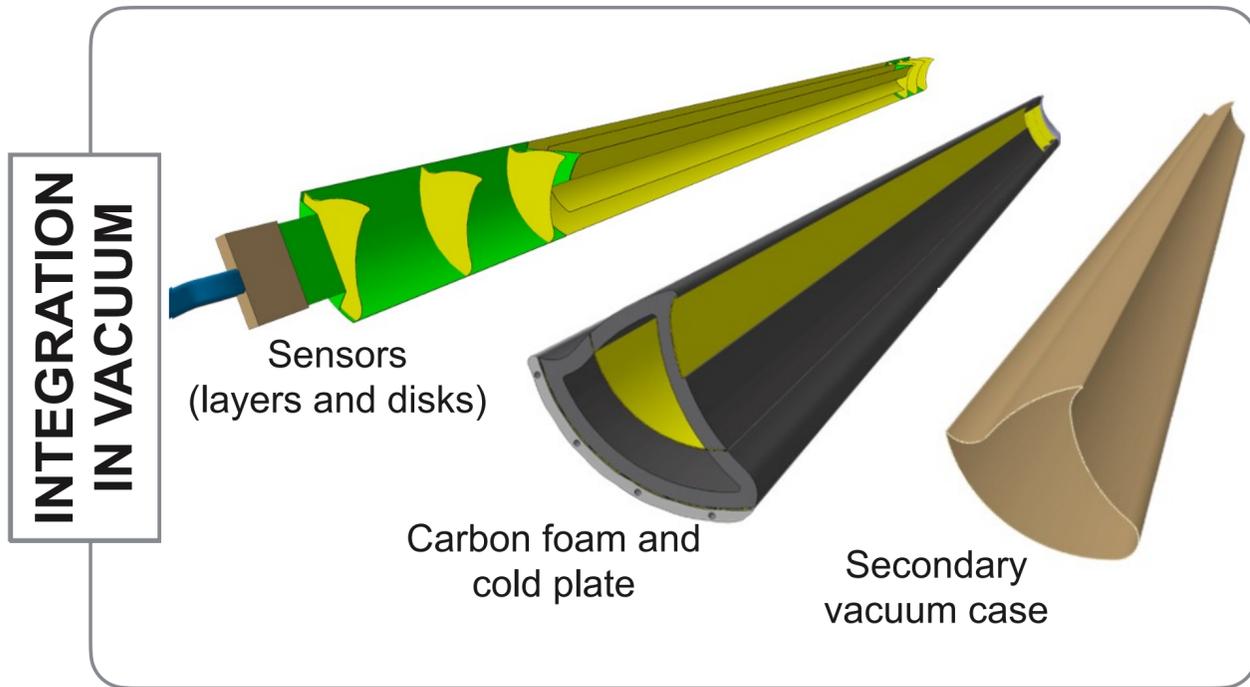
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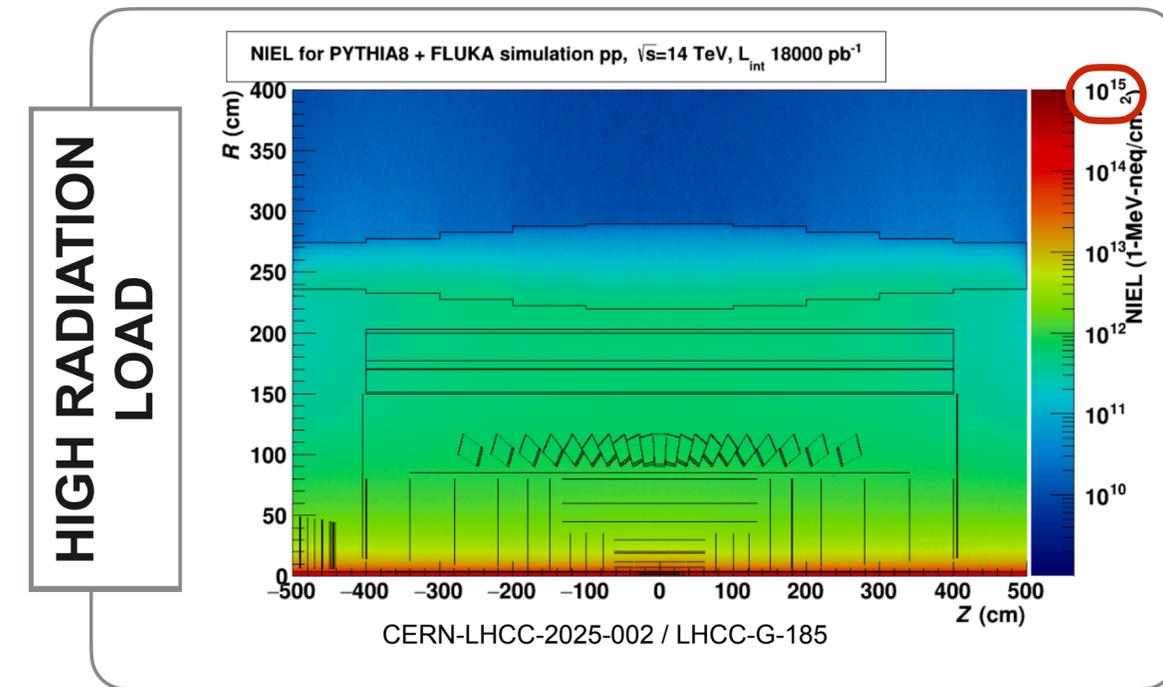
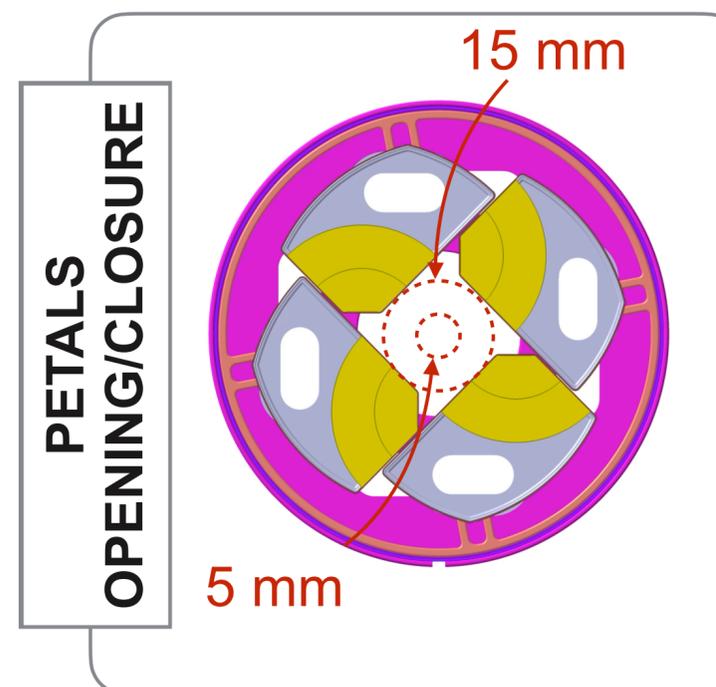
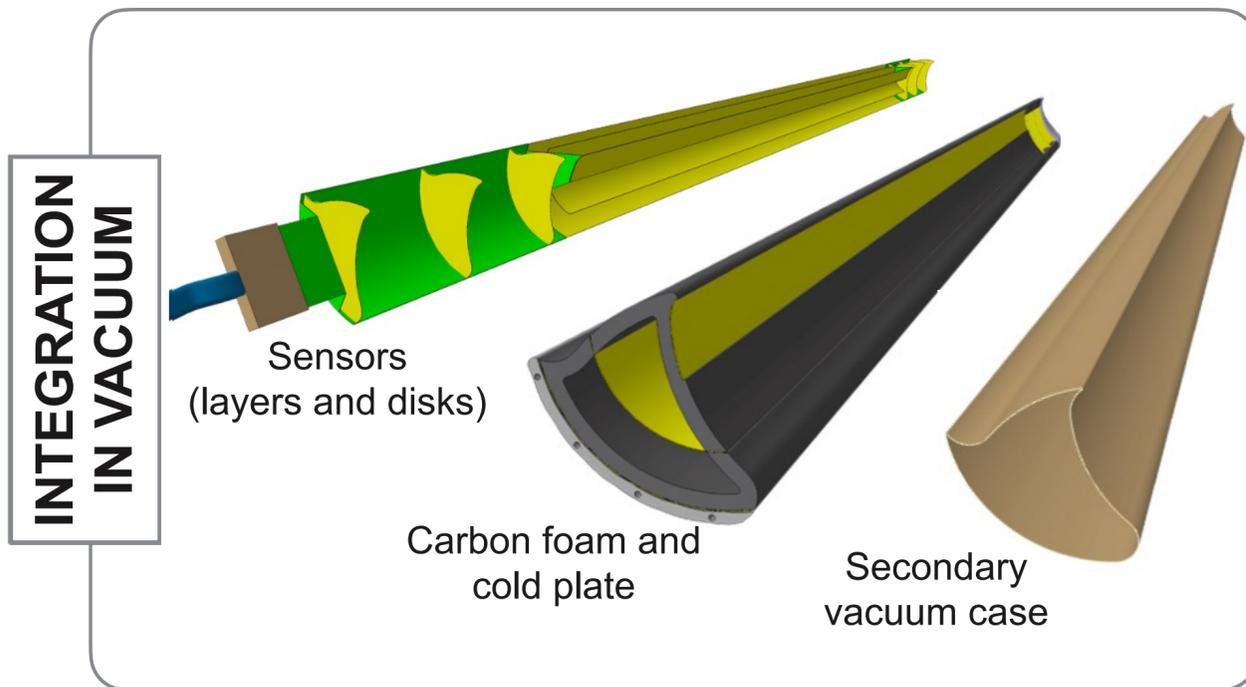
**Move a light-weight vertex detector inside the beam-pipe**



- Technical requirements
  - Bent thin sensors supported by light material (e.g. carbon foam) [mastered within the ITS3 project]
  - Sensors and services integrated in vacuum
  - Movable components to reach minimum distance to primary vertex only during stable beams
  - Sensor performance under high radiation flux



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## R&D for low-mass silicon sensors in vacuum

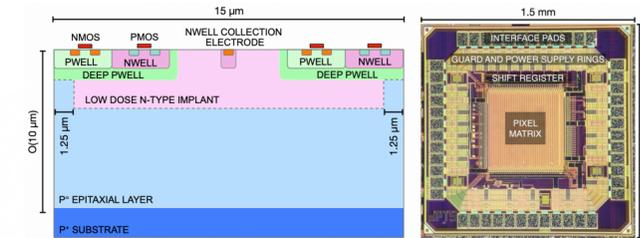
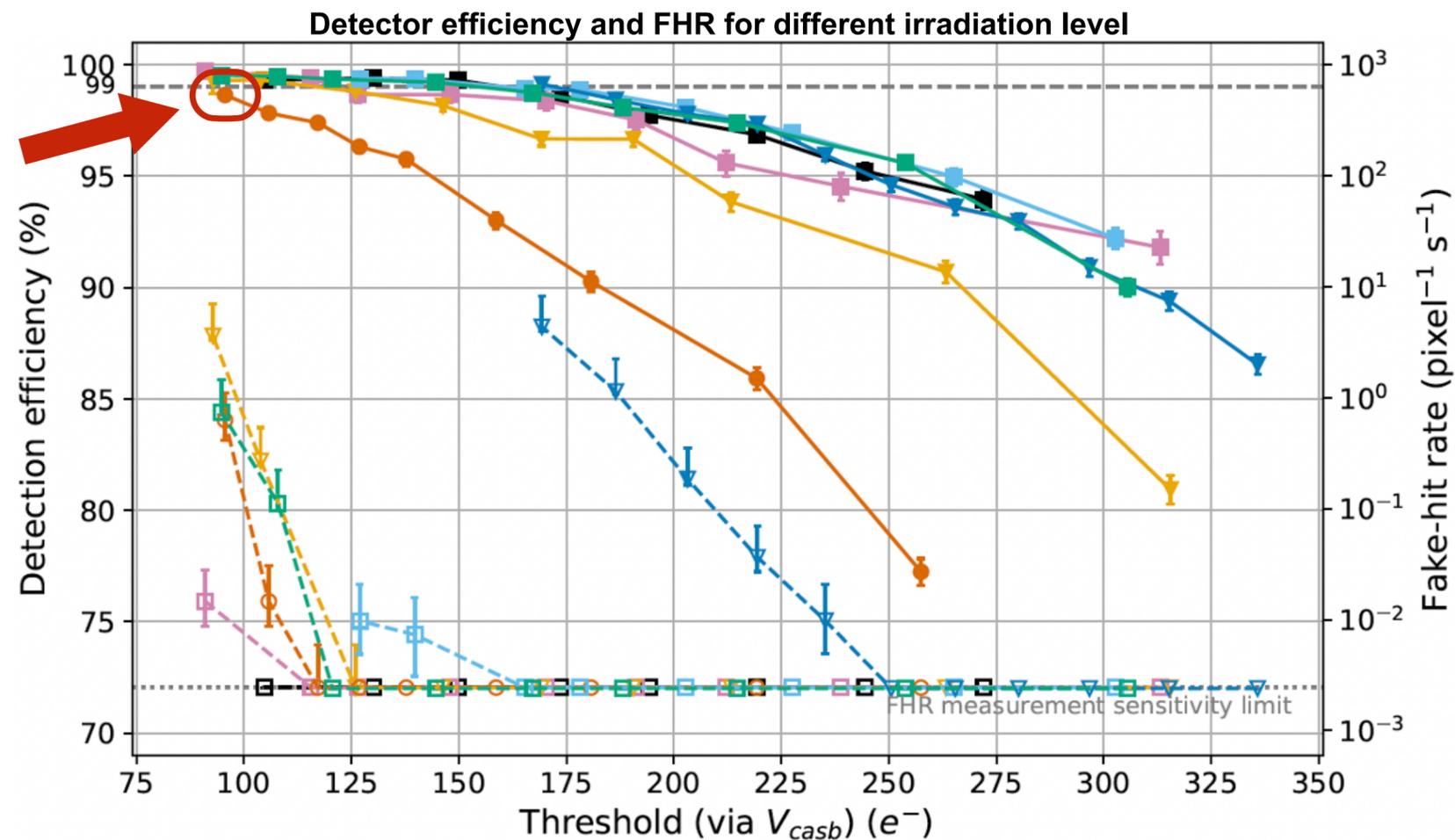
Research objectives

- Enhancing radiation tolerance of CMOS pixel sensors
- In-vacuum integration of sensors

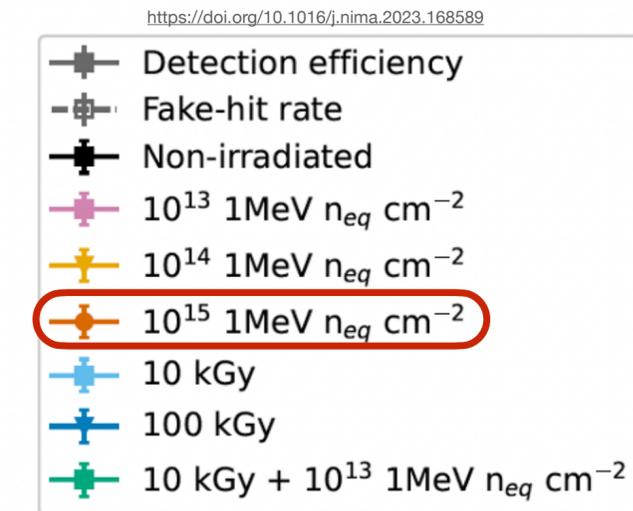
# Research objectives

Enhancing radiation tolerance of CMOS pixel sensors - In-vacuum integration of sensors

- So far demonstrated close to 99% efficiency after irradiation to  $10^{15}$  1 MeV  $n_{eq}/cm^2$ 
  - ALICE ITS3 test chip (DPTS)
  - Operated at room temperature
  - Pixel pitch:  $15 \mu m$

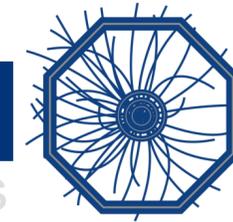


ALICE-ITS3  
MLR1  
DPTS



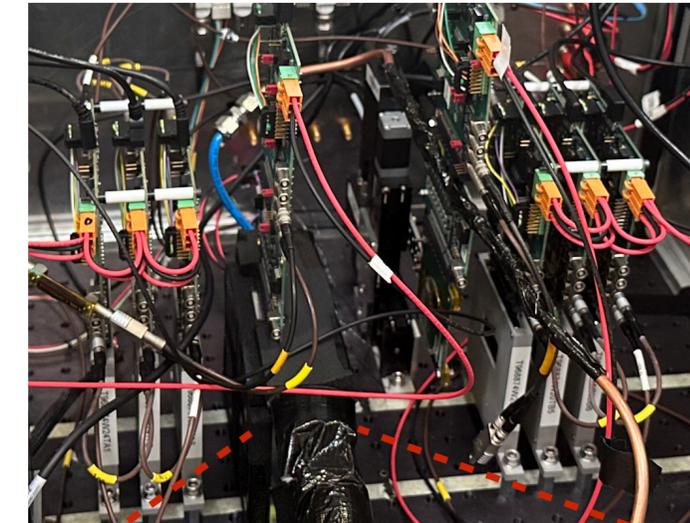
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Enhancing radiation tolerance of CMOS pixel sensors - In-vacuum integration of sensors

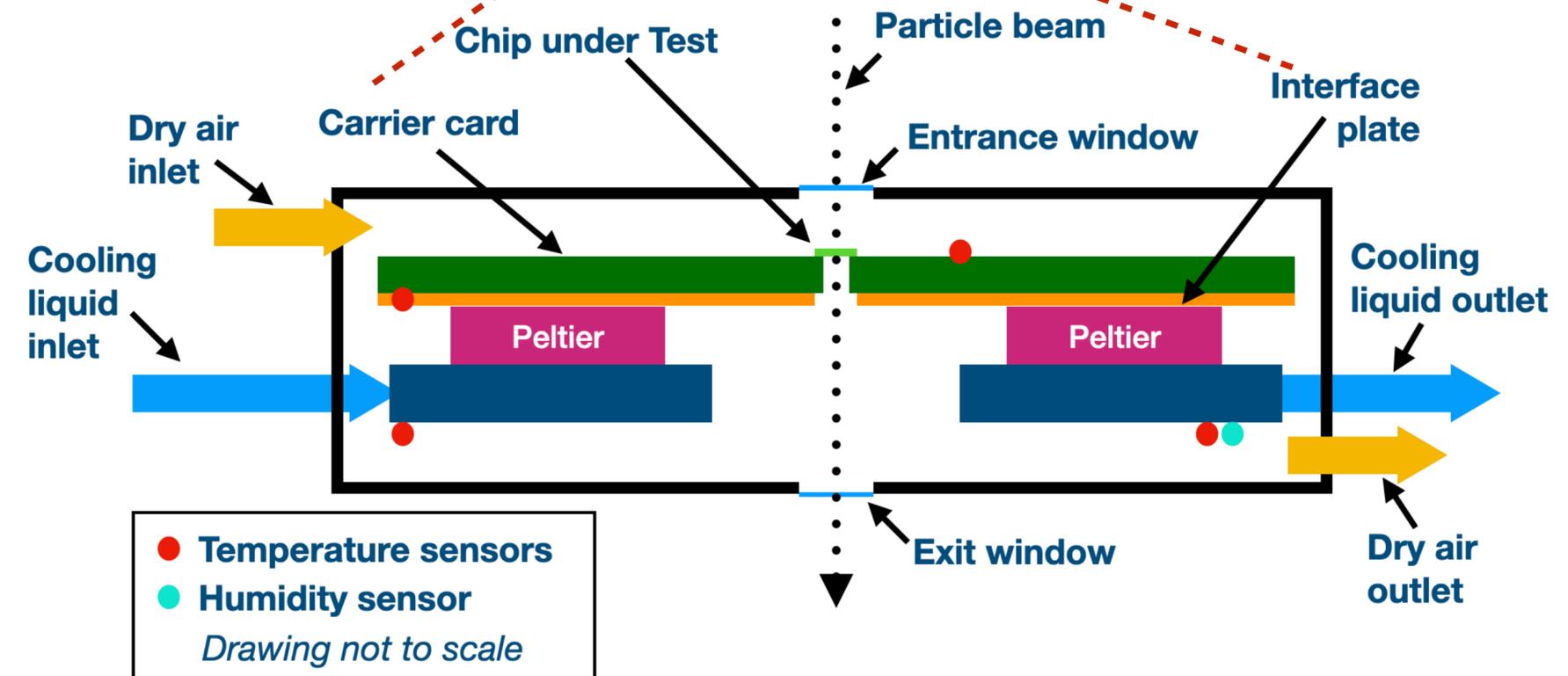


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- What's next?
  - Optimize pixel implant structures
    - variations of existing test chips being submitted
  - Study pitch dependence
    - variations at 10, 12 and 15  $\mu\text{m}$  included in submission
  - Explore behavior at low temperatures
    - cryogenic setups



- **Cryogenic setup** key requirements
  - Thin entrance/exit window
  - Dry air circulation to avoid condensation
  - Temperature range: 15°C to 25°C
  - Monitoring of temperatures and humidity level
  - Based on Peltier elements and liquid cooling
  - Compact to allow use in beam telescopes



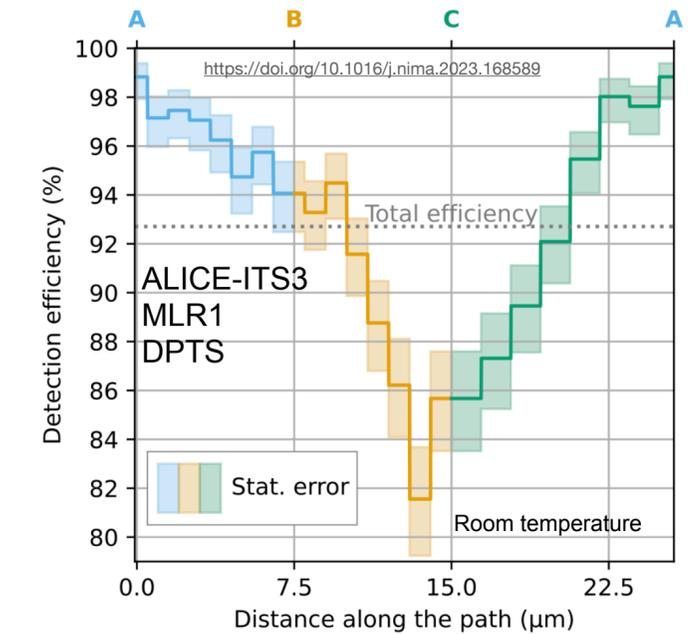
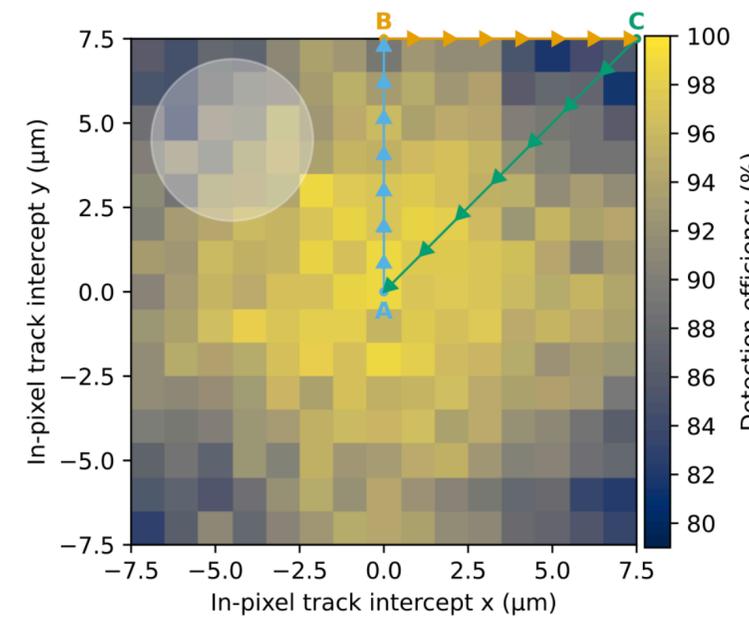
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Enhancing radiation tolerance of CMOS pixel sensors - In-vacuum integration of sensors

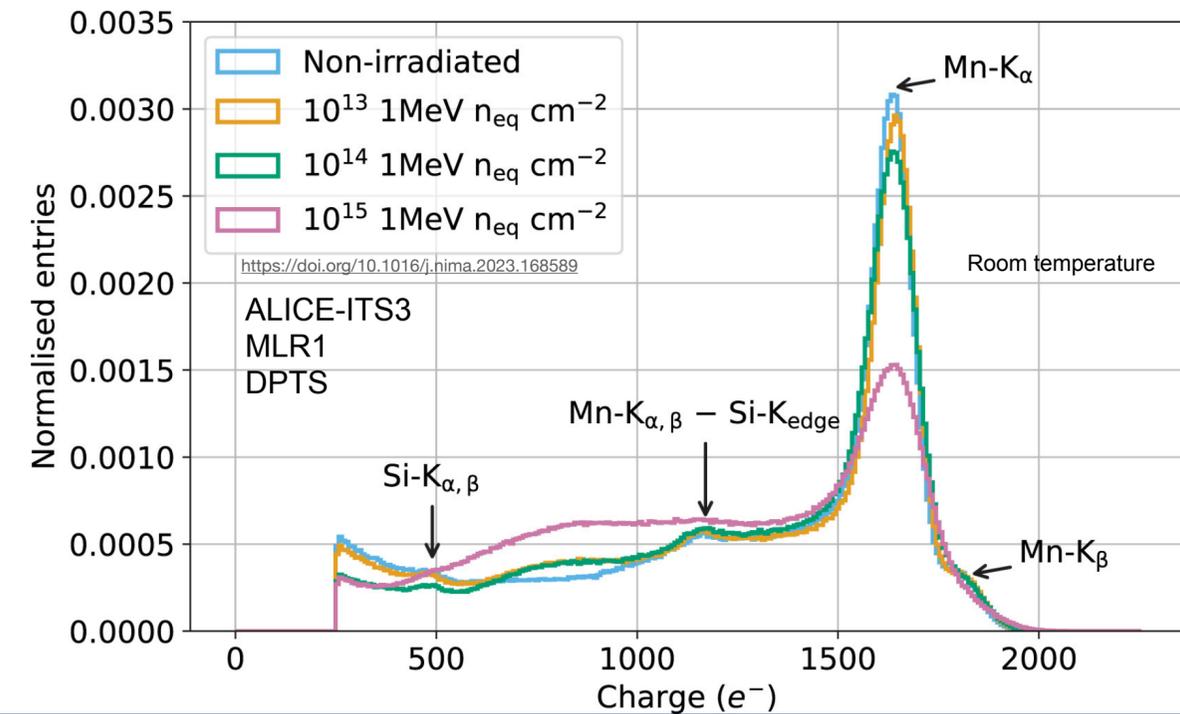


## Studying efficiency in detail: in-pixel measurements

- Probing the charge collection and electric field of a pixel via in pixel efficiency measurements at test beam

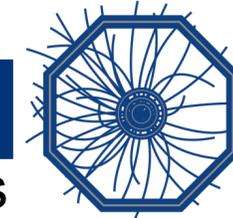


- Systematic comparison of test beam and laboratory measurement results to simulations of the pixel implant structures carried out prior to the chip submission



# Research objectives

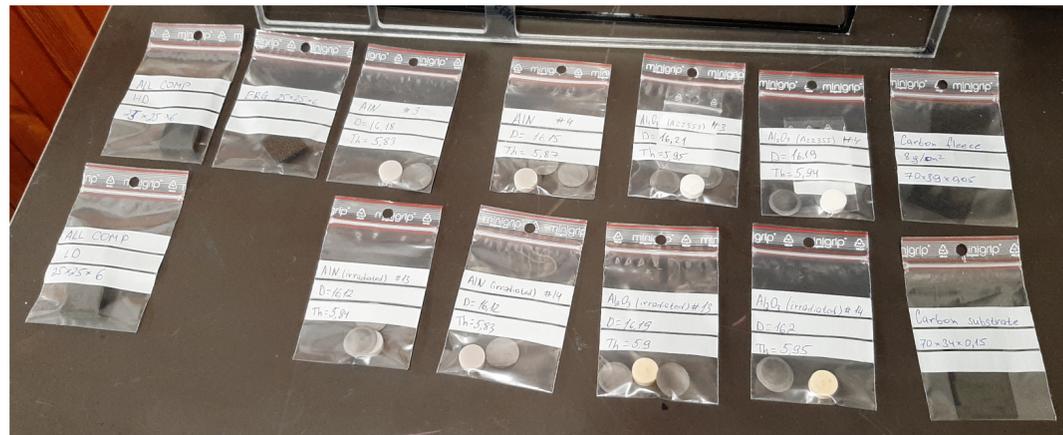
Enhancing radiation tolerance of CMOS pixel sensors - In-vacuum integration of sensors



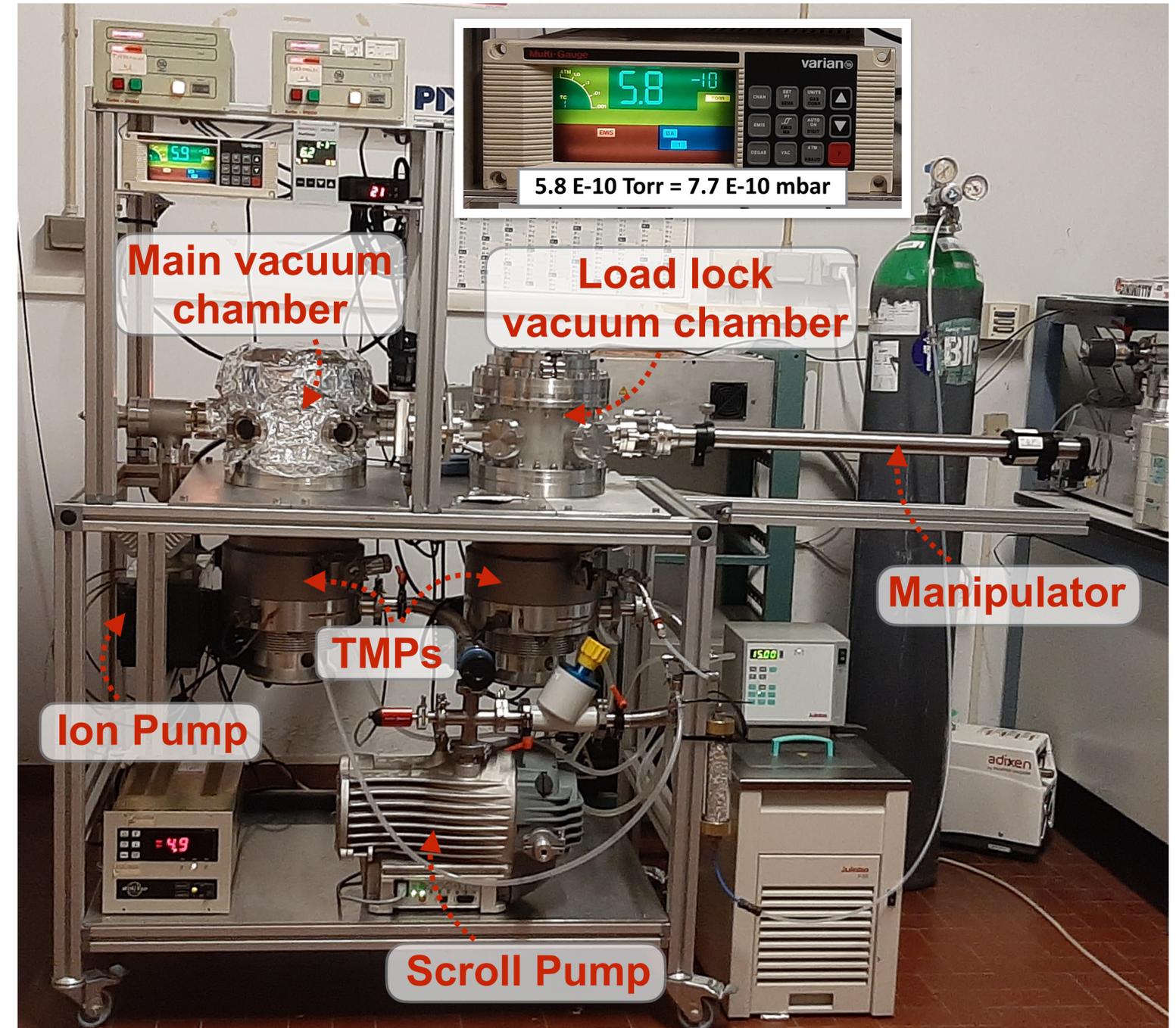
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- UHV setup assembled in Bari
  - Characterization campaign ongoing on a large preliminary set of materials



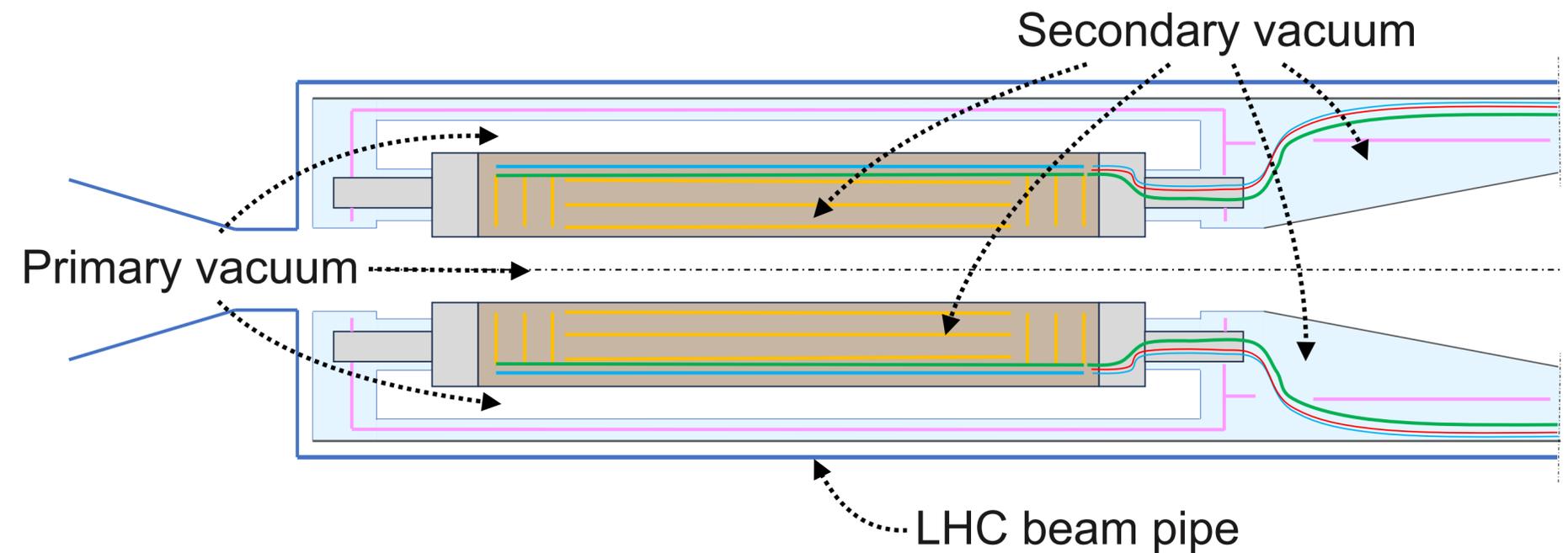
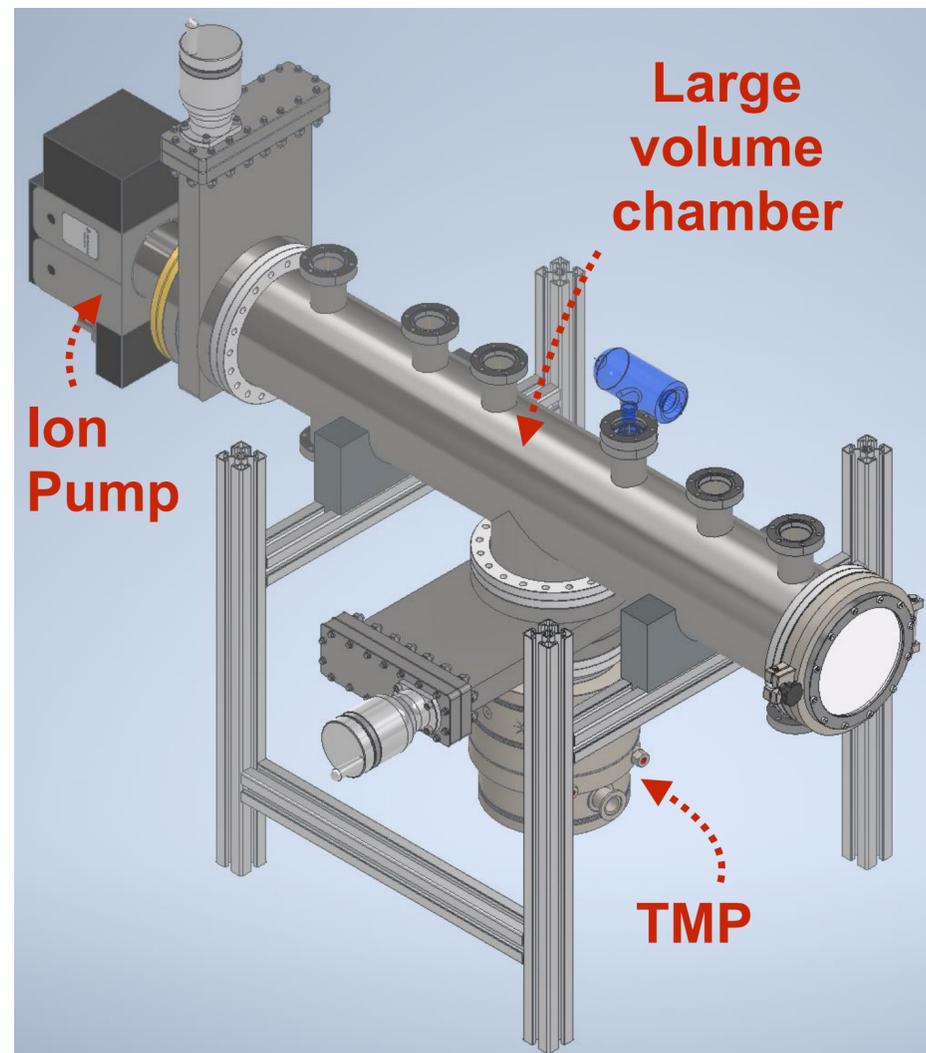
- carbon foam
- 3D printed aluminium nitride (AlN), alumina ( $\text{Al}_2\text{O}_3$ ) and silumin (AlSi)
- optical fiber
- Si wafer
- standard flex circuit



# Research objectives

Enhancing radiation tolerance of CMOS pixel sensors - In-vacuum integration of sensors

- What's next?
  - Outgassing studies for a full IRIS prototype → New large volume setup
  - Outgassing studies from internal material (into secondary vacuum) and external wall (into primary vacuum)



IRIS early prototype

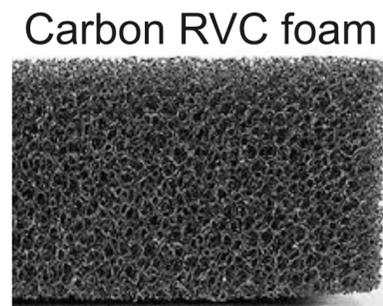
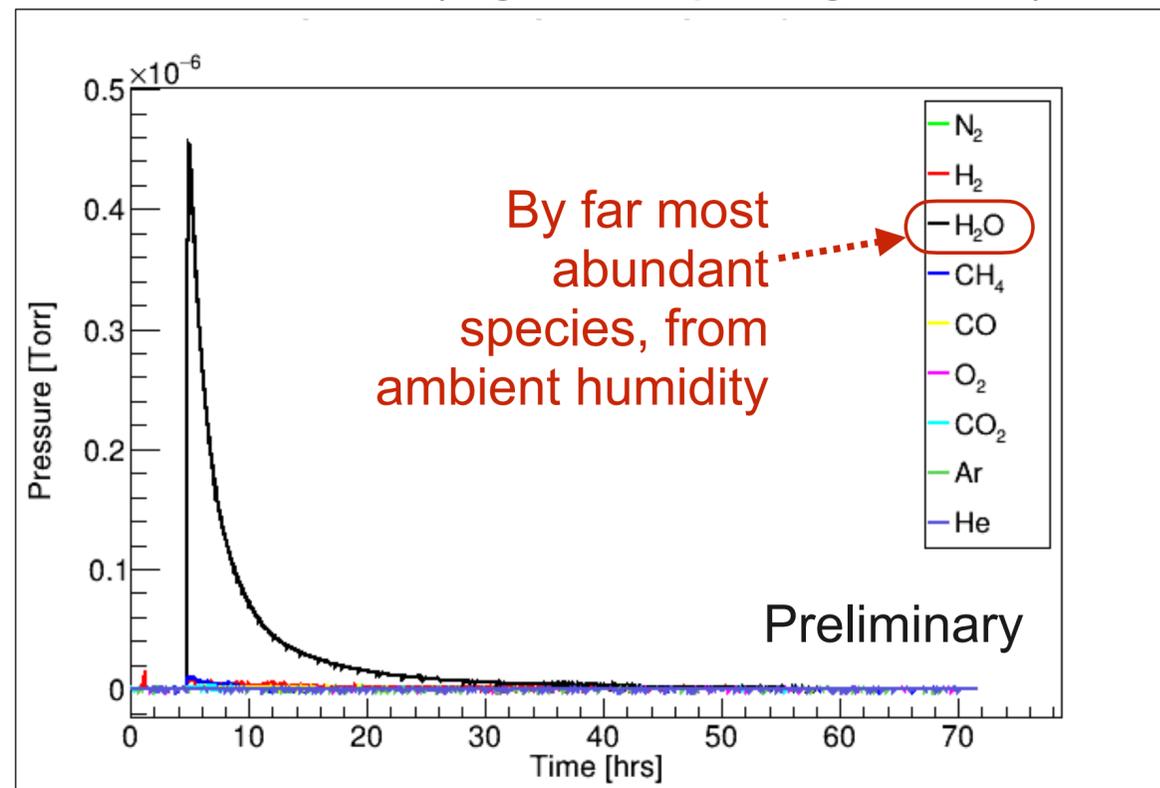
# Research objectives

Enhancing radiation tolerance of CMOS pixel sensors - In-vacuum integration of sensors

How to **identify and treat outgassing components** based on well established procedures:

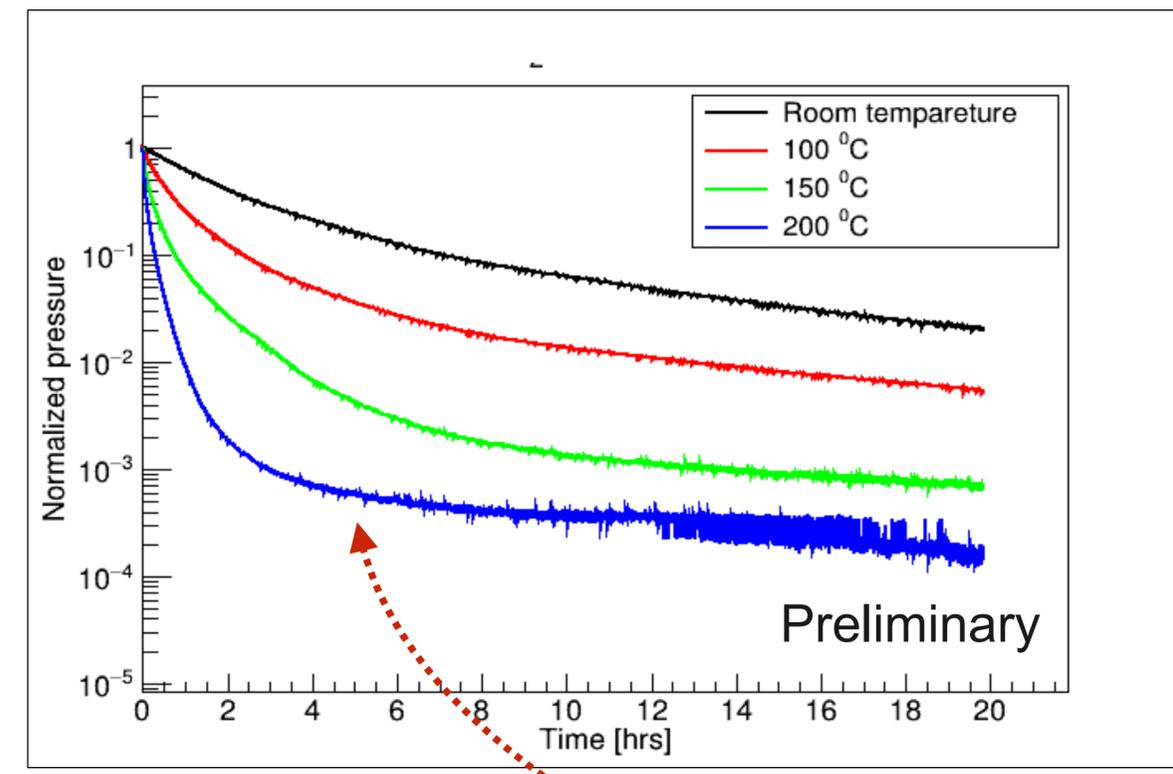
## Residual Gas Analysis (RGA)

Identify desorbed species from detector materials  
→ Help understanding outgassing due to mechanical movements (e.g. IRIS opening/closure)

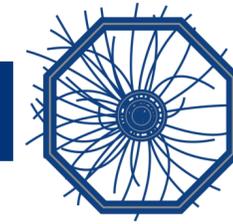


## Thermal Desorption Spectroscopy (TDS)

Monitoring the species desorbing during heat treatment under vacuum → Help defining handling procedure during detector construction

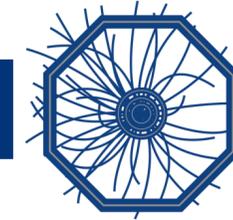


<b>Personnel</b>	85 k€/year	2 or 3 PhD (different costs in Italy and at CERN)		
<b>Travel support and workshops</b>	10 k€/year	Start-up and wrap-up workshops		
<b>Consumables/ Hardware</b>	30 k€/year	Radiation studies	• Planning to prepare samples (thinning@dicing, carrier cards, wire bonding, irradiation)	8 k€
			• Procurement of new readout systems providing higher bandwidth and sampling rate	60 k€
			• Mechanics (raw material + work)	20 k€
		Vacuum studies	• Large volume vacuum chamber, flanges, gate valves and consumables	12 k€
			• Turbo and ion pumps	20 k€
<b>Indirect cost</b>	31 k€/year	25% of the direct costs		
<b>TOTAL per year</b>		156 k€/year		
<b>TOTAL (4 year)</b>		<b>624 k€</b>		



# Research objectives

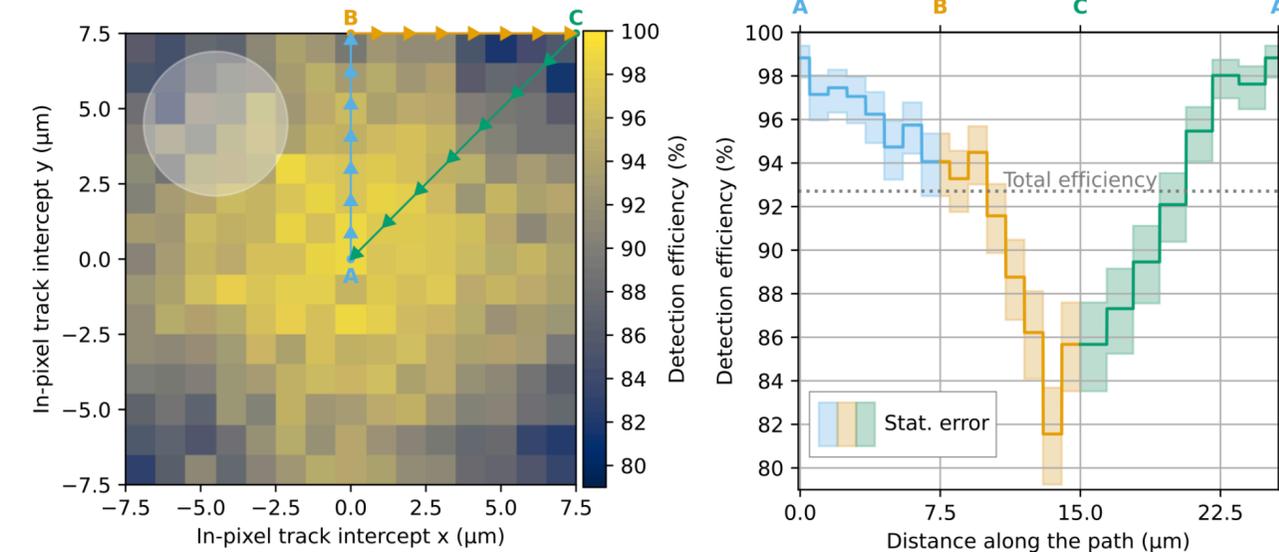
Enhancing radiation tolerance of CMOS pixel sensors



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How to **study efficiency in detail**, based on prior experience with ITS2/3:

- Probing the electric field configuration and the charge collection of pixel via in pixel efficiency through test beam measurements
- Complementing with laboratory measurements with radioactive source (Fe-55, Sr-90)
- Comparison to simulations



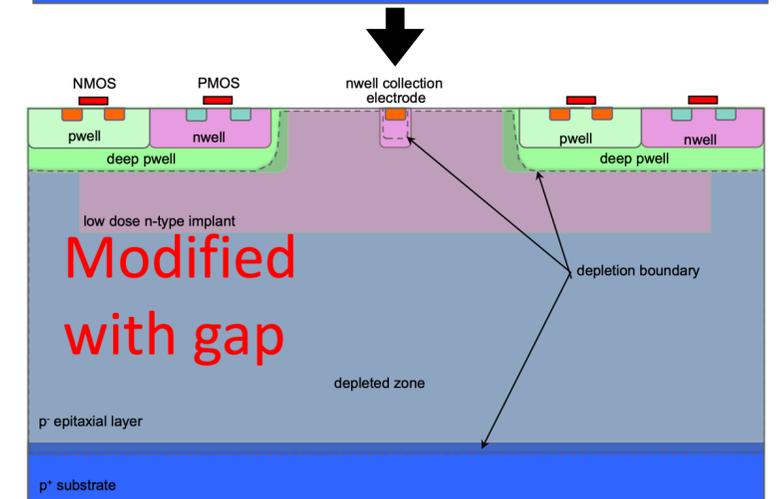
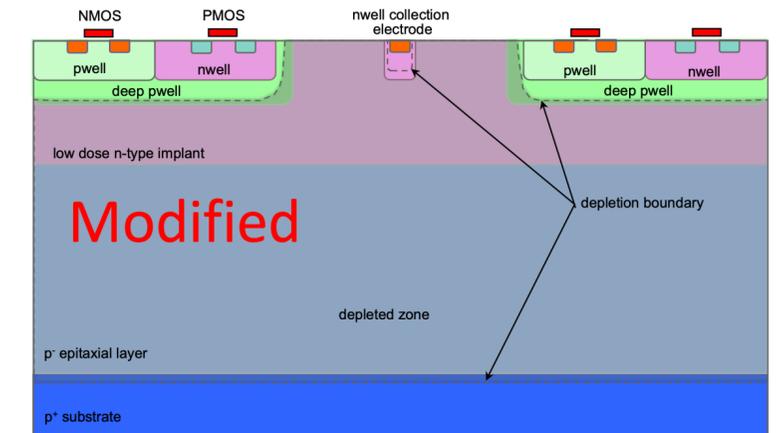
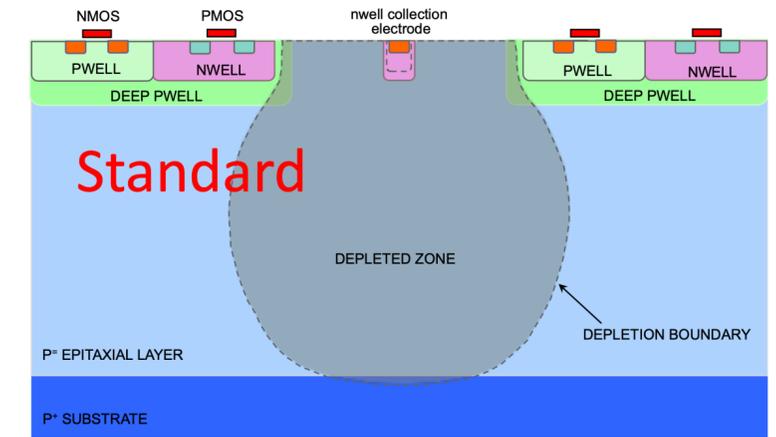
New slide: “Studying efficiency in detail”

- In-pixel efficiency plot -> probing the field configuration and charge collection of the pixel
- Comparison to simulations:
  - Pixel implant structure variations have been simulated prior to submission
  - Laboratory measurements with radioactive sources (Fe-55, Sr-90) complementing the test beam measurementsAlso saying based on prior experience with ITS2/3

# Research objectives

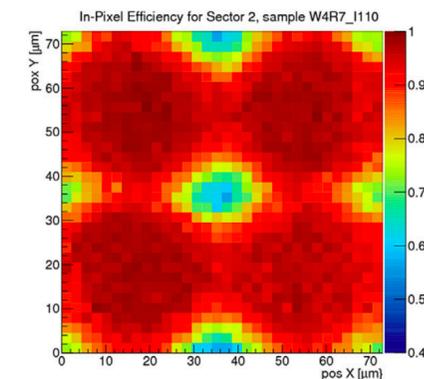
## Enhancing radiation tolerance of CMOS pixel sensors

- It has been shown that changing the doping profile of the epitaxial layer, the radiation hardness of MAPS can be improved
  - **Standard process** → Operational up to  $10^{13}$  1 MeV  $n_{eq}/cm^2$
  - **Modified process** → Operational up to  $10^{14}$  1 MeV  $n_{eq}/cm^2$ 
    - additional deep blanket low doped implant over the full pixel area
  - **Modified with gap process** → Operational up to  $10^{15}$  1 MeV  $n_{eq}/cm^2$ 
    - gap in the deep low dose n-implant

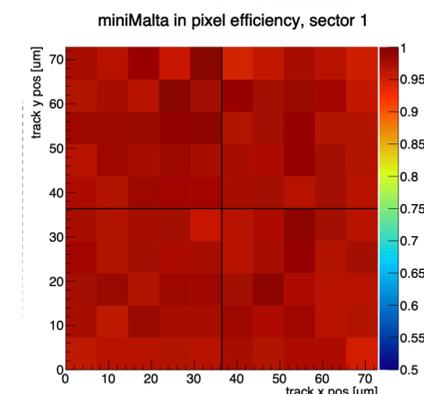


J. NIMA 871 (2017) 90-96  
J. NIMA 958 (2020) 162404

2019 JINST 14 C05013  
2020 JINST 15 P0200



In pixel efficiency in a 2x2 matrix MALTA sensor

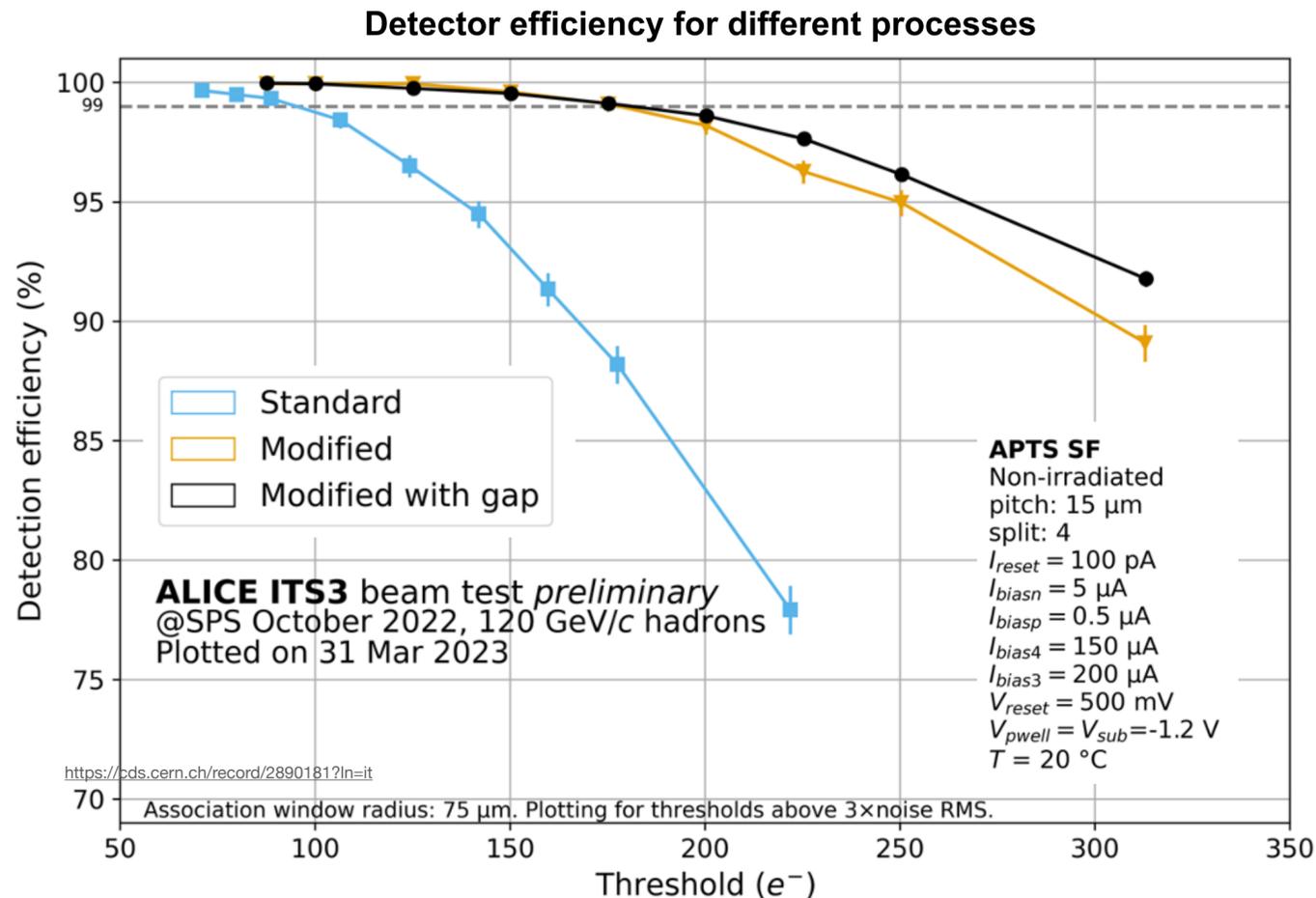
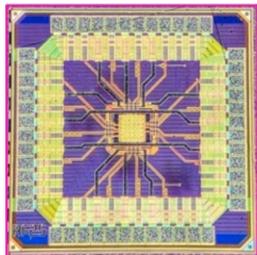


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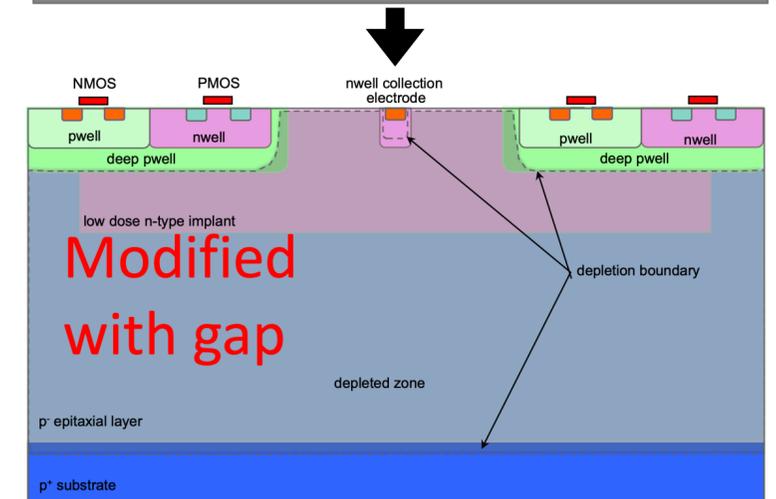
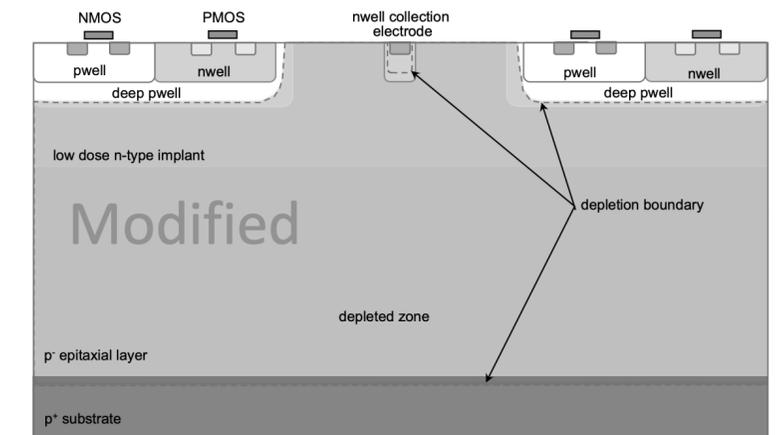
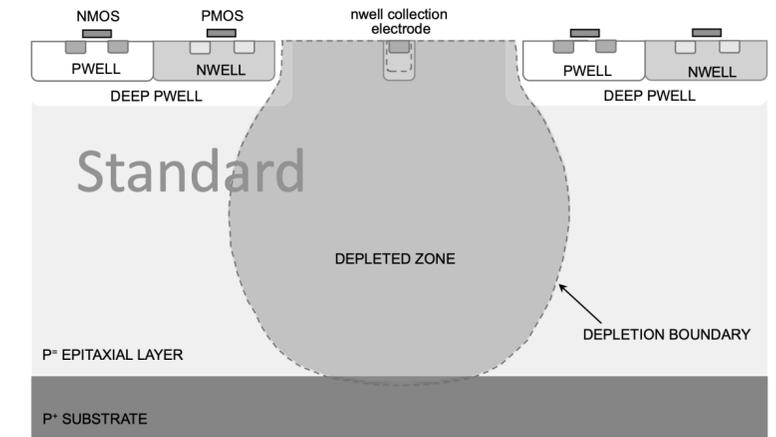
ALICE-ITS3  
MLR1  
APTS



# Research objectives

## Enhancing radiation tolerance of CMOS pixel sensors

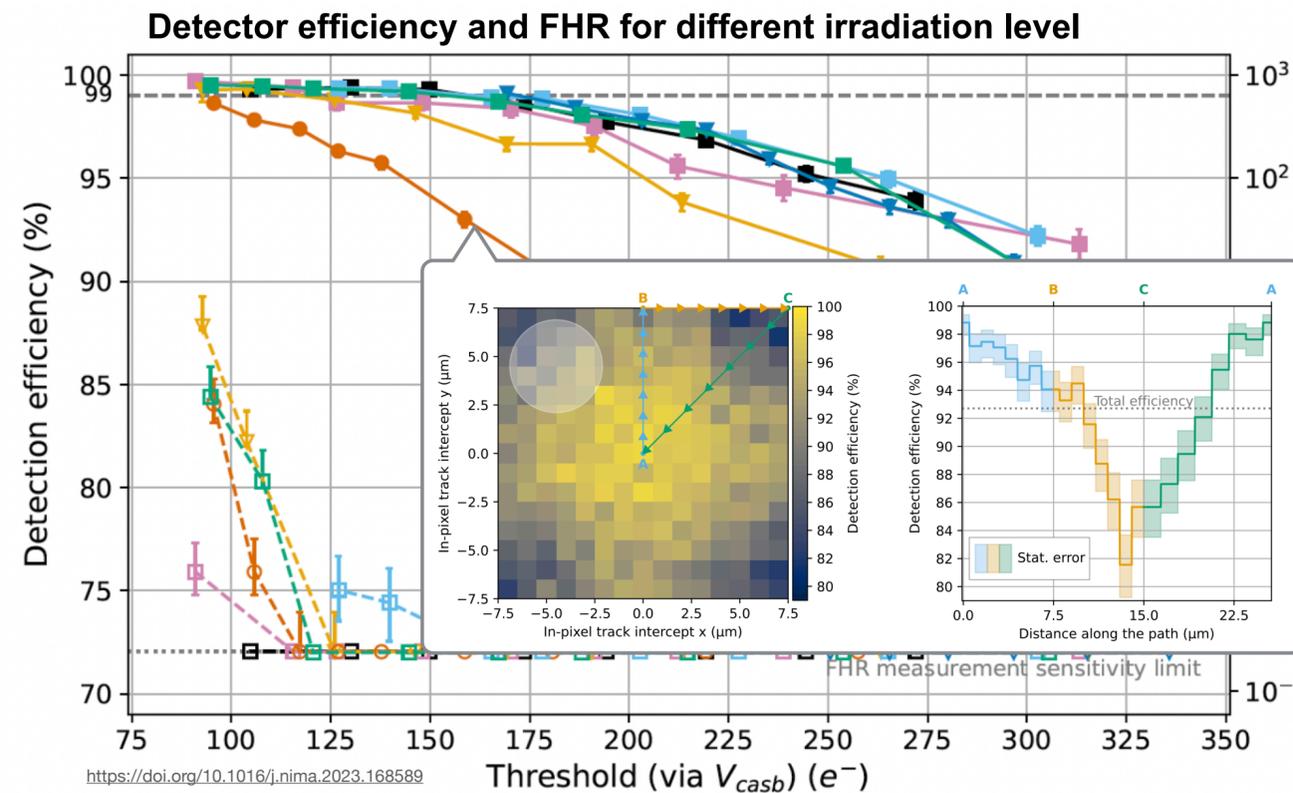
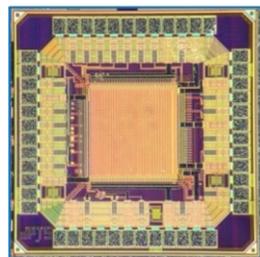
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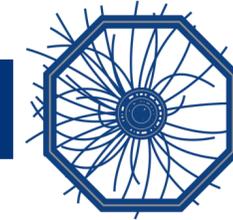
ALICE-ITS3  
MLR1  
DPTS



- Detection efficiency
- Fake-hit rate
- Non-irradiated
- $10^{13} \text{ 1MeV } n_{eq} \text{ cm}^{-2}$
- $10^{14} \text{ 1MeV } n_{eq} \text{ cm}^{-2}$
- $10^{15} \text{ 1MeV } n_{eq} \text{ cm}^{-2}$
- 10 kGy
- 100 kGy
- 10 kGy +  $10^{13} \text{ 1MeV } n_{eq} \text{ cm}^{-2}$

# Research objectives

In-vacuum integration of pixel sensors



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